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				Application Number	10/582,035-Conf. #1665		
INF	ORMATION	l DI	SCLOSURE	Filing Date	May 7, 2007		
ST	ATEMENT E	3Y /	APPLICANT	First Named Inventor	Shen		
_				Art Unit	4146		
	(Use as many she	eets as	necessary)	Examiner Name	R. T. Huber		

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Examiner		/Robert I	Huber/				Date Considered		02/05/2009		

<sup>\*</sup>EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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